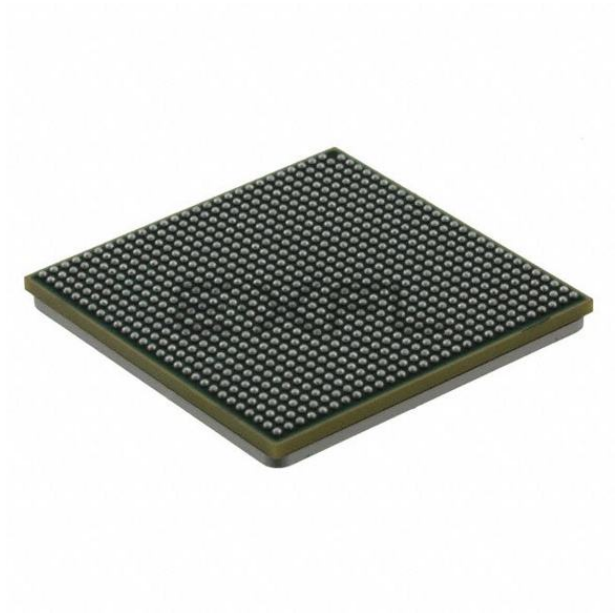

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.5GHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR2, DDR3
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	SATA 3Gbps (2)
USB	USB 2.0 (3)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 90°C (TA)
Security Features	Cryptography
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8536eavjavla

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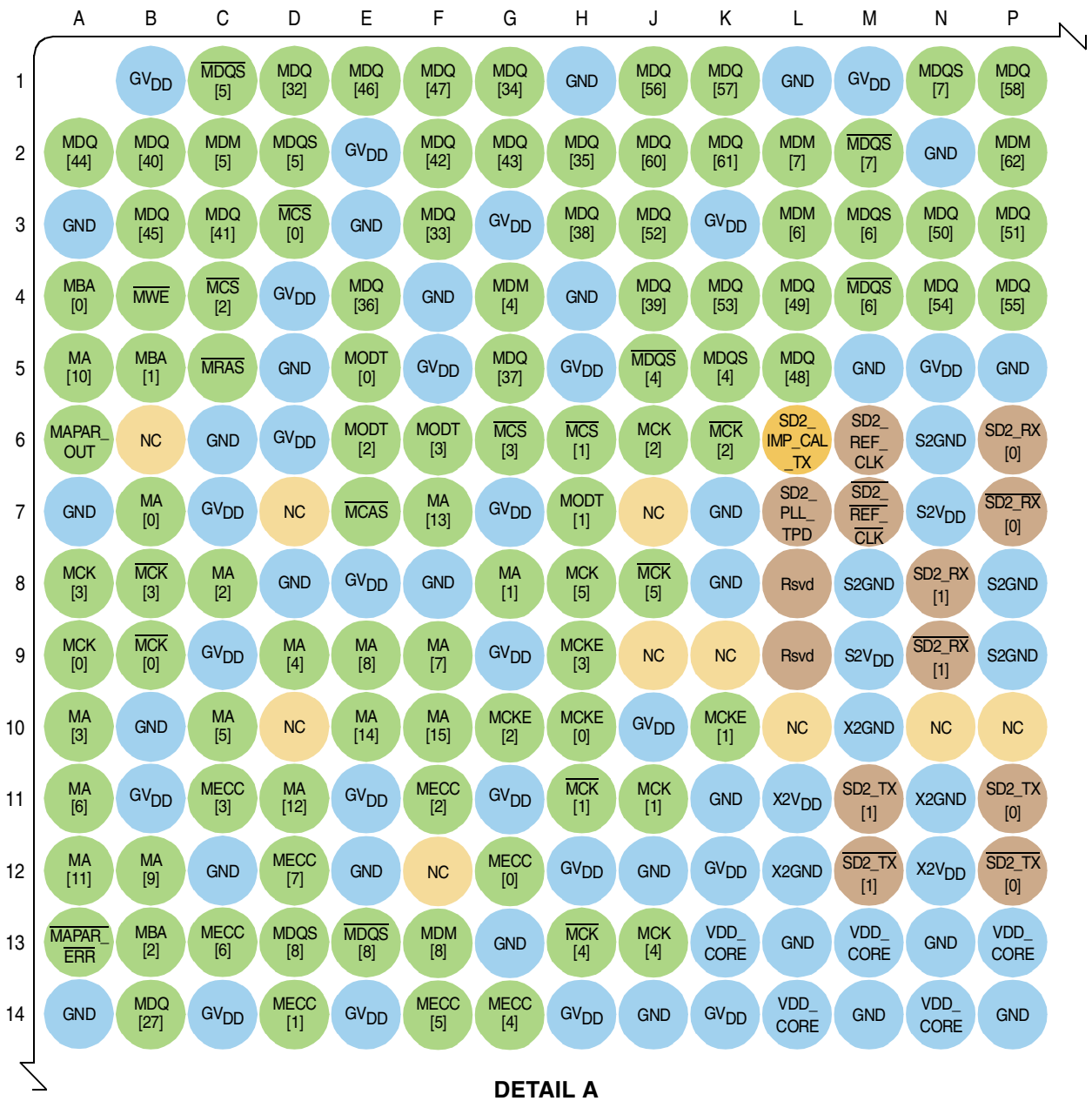


DETAIL A

Figure 3. Chip Pin Map Detail A

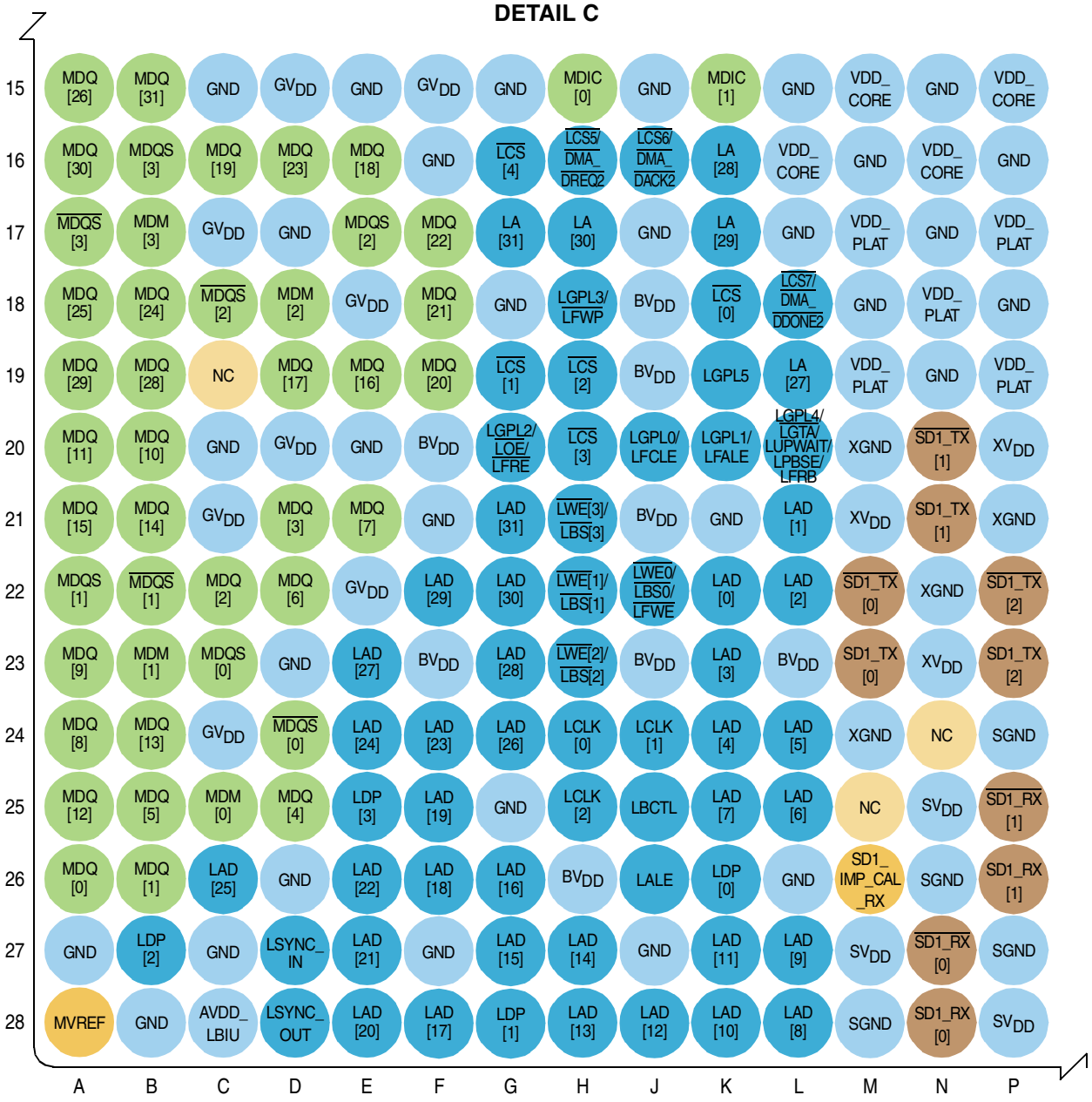


Figure 5. Chip Pin Map Detail C

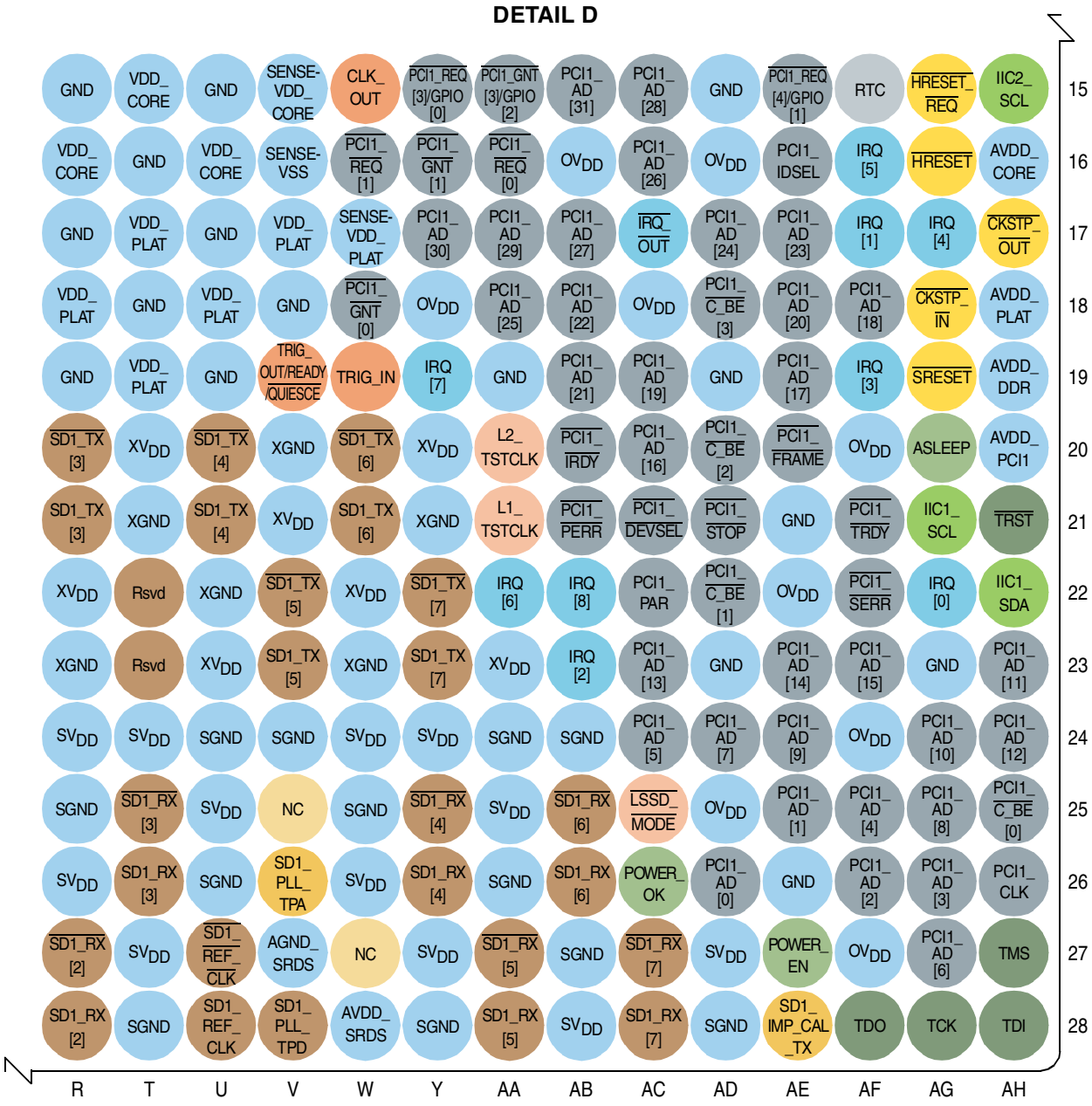
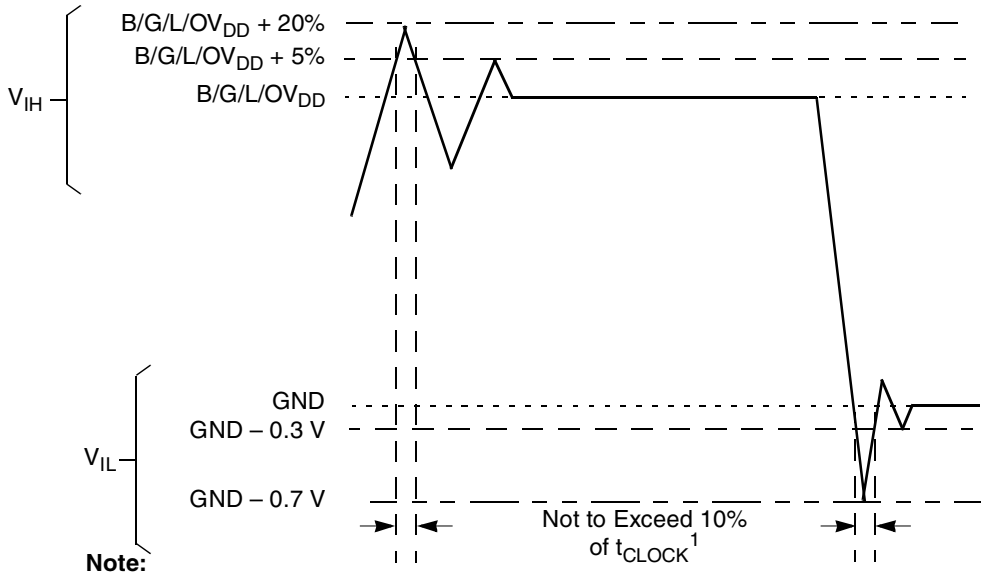


Figure 6. Chip Pin Map Detail D

Table 1. Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
General-Purpose Input/Output					
GPIO[0:1]/PCI1_REQ[3:4]	GPIO/PCI request	Y15,AE15	I/O	OV_{DD}	—
GPIO[2:3]/PCI1_GNT[3:4]	GPIO/PCI grant	AA15,AC14	I/O	OV_{DD}	—
GPIO[4]/SDHC_CD	GPIO/SDHC card detection	AH11	I/O	OV_{DD}	—
GPIO[5]/SDHC_WP	GPIO/SDHC write protection	AG10	I/O	OV_{DD}	32
GPIO[6]/USB1_PCTL0	GPIO/USB1 PCTL0	AC3	I/O	OV_{DD}	—
GPIO[7]/USB1_PCTL1	GPIO/USB1 PCTL1	AC4	I/O	OV_{DD}	—
GPIO[8]/USB2_PCTL0	GPIO/USB2 PCTL0	AG9	I/O	OV_{DD}	—
GPIO[9]/USB2_PCTL1	GPIO/USB2 PCTL1	AC9	I/O	OV_{DD}	—
GPIO[10:11] /DMA_DACK[0:1]	GPIO/DMA Ack	AD6,AE10	I/O	OV_{DD}	—
GPIO[12:13] /DMA_DDONE[0:1]	GPIO/DMA done	AA11,AB11	I/O	OV_{DD}	—
GPIO[14:15] /DMA_DREQ[0:1]	GPIO/DMA request	AB10,AD11	I/O	OV_{DD}	—
System Control					
HRESET	Hard reset	AG16	I	OV_{DD}	—
HRESET_REQ	Hard reset - request	AG15	O	OV_{DD}	22
SRESET	Soft reset	AG19	I	OV_{DD}	—
CKSTP_IN	CheckStop in	AG18	I	OV_{DD}	—
CKSTP_OUT	CheckStop Output	AH17	O	OV_{DD}	2,4
Debug					
TRIG_IN	Trigger in	W19	I	OV_{DD}	—
TRIG_OUT/READY /QUIESCE	Trigger out/Ready/Quiesce	V19	O	OV_{DD}	22
MSRCID[0:1]	Memory debug source port ID	W12,W13	O	OV_{DD}	6,9
MSRCID[2:4]	Memory debug source port ID	V12, W14,W11	O	OV_{DD}	6,9,22
MDVAL	Memory debug data valid	V13	O	OV_{DD}	6,22
CLK_OUT	Clock Out	W15	O	OV_{DD}	11
Clock					
RTC	Real time clock	AF15	I	OV_{DD}	—
SYSCLK	System clock / PCI clock	AH14	I	OV_{DD}	—
DDRCLK	DDR clock	AC13	I	OV_{DD}	30
JTAG					

This figure shows the undershoot and overshoot voltages at the interfaces of the chip.



Note:

1. t_{CLOCK} refers to the clock period associated with the respective interface:
   For I^2C and JTAG, t_{CLOCK} references SYSCLK.
   For DDR, t_{CLOCK} references MCLK.
   For eTSEC, t_{CLOCK} references EC_GTX_CLK125.
   For eLBC, t_{CLOCK} references LCLK.
   For PCI, t_{CLOCK} references PCI1_CLK or SYSCLK.

2. With the PCI overshoot allowed (as specified above), the device does not fully comply with the maximum AC ratings and device protection guideline outlined in the PCI rev. 2.2 standard (section 4.2.2.3).

Figure 7. Overshoot/Undershoot Voltage for $GV_{DD}/OV_{DD}/LV_{DD}$

The core voltage must always be provided at nominal 1.0 V . (See Table 3 for actual recommended core voltage). Voltage to the processor interface I/Os are provided through separate sets of supply pins and must be provided at the voltages shown in Table 3. The input voltage threshold scales with respect to the associated I/O supply voltage. OV_{DD} and LV_{DD} based receivers are simple CMOS I/O circuits and satisfy appropriate LVCMOS type specifications. The DDR2 and DDR3 SDRAM interface uses differential receivers referenced by the externally supplied MVREF*n* signal (nominally set to GVDD/2) as is appropriate for the SSTL_1.8 electrical signaling standard for DDR2 or 1.5-V electrical signaling for DDR3. The DDR DQS receivers cannot be operated in single-ended fashion. The complement signal must be properly driven and cannot be grounded.

2.4.4 eTSEC Gigabit Reference Clock Timing

This table provides the eTSEC gigabit reference clocks (EC_GTX_CLK125) AC timing specifications for the chip.

Table 8. EC_GTX_CLK125 AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
EC_GTX_CLK125 frequency	f_{G125}	—	125	—	MHz	—
EC_GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	—
EC_GTX_CLK rise and fall time LV_{DD}, TV_{DD} = 2.5V LV_{DD}, TV_{DD} = 3.3V	t_{G125R}/t_{G125F}	—	—	 0.75 1.0	ns	1
EC_GTX_CLK125 duty cycle GMII, TBI 1000Base-T for RGMII, RTBI	t_{G125H}/t_{G125}	 45 47	—	 55 53	%	2

Notes:

1. Rise and fall times for EC_GTX_CLK125 are measured from 0.5V and 2.0V for L/TVDD=2.5V, and from 0.6 and 2.7V for L/TVDD=3.3V at 0.6 V and 2.7 V.
2. EC_GTX_CLK125 is used to generate the GTX clock for the eTSEC transmitter with 2% degradation. EC_GTX_CLK125 duty cycle can be loosened from 47/53% as long as the PHY device can tolerate the duty cycle generated by the eTSEC GTX_CLK. See Section 2.9.2.6, "RGMII and RTBI AC Timing Specifications," for duty cycle for 10Base-T and 100Base-T reference clock.

2.4.5 DDR Clock Timing

This table provides the DDR clock (DDRCLK) AC timing specifications for the chip.

Table 9. DDRCLK AC Timing Specifications

At recommended operating conditions with OV_{DD} of 3.3V ± 5%.

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
DDRCLK frequency	f_{DDRCLK}	66	—	166	MHz	1
DDRCLK cycle time	t_{DDRCLK}	6.0	—	15.15	ns	—
DDRCLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	1.2	ns	2
DDRCLK duty cycle	t_{KHK}/t_{DDRCLK}	40	—	60	%	—
DDRCLK jitter	—	—	—	+/– 150	ps	3, 4

Notes:

1. **Caution:** The DDR complex clock to DDRCLK ratio settings must be chosen such that the resulting DDR complex clock frequency does not exceed the maximum or minimum operating frequencies. See Section 2.23.4, "DDR/DDRCLK PLL Ratio," for ratio settings.
2. Rise and fall times for DDRCLK are measured at 0.6 V and 2.7 V.
3. The DDRCLK driver's closed loop jitter bandwidth should be <500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track DDRCLK drivers with the specified jitter.
4. For spread spectrum clocking, guidelines are +0% to –1% down spread at a modulation rate between 20 kHz and 60 kHz on DDRCLK.

2.6.2.2 DDR2 and DDR3 SDRAM Interface Output AC Timing Specifications

This table contains the output AC timing targets for the DDR2 and DDR3 SDRAM interface.

Table 19. DDR SDRAM Output AC Timing Specifications

At recommended operating conditions with GV_{DD} of 1.8 V ± 5% for DDR2 or 1.5 V ± 5% for DDR3.

Parameter	Symbol [1]	Min	Max	Unit	Notes
MCK[n] cycle time, MCK[n]/$\overline{\text{MCK}}$[n] crossing	t_{MCK}	3.0	5	ns	2
ADDR/CMD output setup with respect to MCK	t_{DDKHAS}			ns	3
667 MHz		1.10	—		7
533 MHz		1.48	—		
400 MHz		1.95	—		
ADDR/CMD output hold with respect to MCK	t_{DDKHAX}			ns	3
667 MHz		1.10	—		7
533 MHz		1.48	—		
400 MHz		1.95	—		
$\overline{\text{MCS}}$[n] output setup with respect to MCK	t_{DDKHCS}			ns	3
667 MHz		1.10	—		7
533 MHz		1.48	—		
400 MHz		1.95	—		
$\overline{\text{MCS}}$[n] output hold with respect to MCK	t_{DDKHCX}			ns	3
667 MHz		1.10	—		7
533 MHz		1.48	—		
400 MHz		1.95	—		
MCK to MDQS Skew	t_{DDKHMH}			ns	4
<= 667 MHz		–0.6	0.6		7
MDQ/MECC/MDM output setup with respect to MDQS	t_{DDKHDS}, t_{DDKLDS}			ps	5
667 MHz		450	—		7
533 MHz		538	—		
400 MHz		700	—		
MDQ/MECC/MDM output hold with respect to MDQS	t_{DDKHDX}, t_{DDKLDX}			ps	5
667 MHz		450	—		7
533 MHz		538	—		
400 MHz		700	—		
MDQS preamble start	t_{DDKHMP}			ns	6

This figure provides the AC test load for the DDR bus.

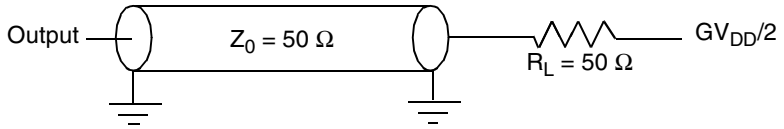


Figure 11. DDR AC Test Load

2.7 eSPI

This section describes the DC and AC electrical specifications for the eSPI of the chip.

2.7.1 eSPI DC Electrical Characteristics

This table provides the DC electrical characteristics for the chip eSPI.

Table 20. SPI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V ≤ V_{IN} ≤ OV_{DD}	—	±10	μA

2.7.2 eSPI AC Timing Specifications

This table and provide the eSPI input and output AC timing specifications.

Table 21. SPI AC Timing Specifications[1]

Characteristic	Symbol [2]	Min	Max	Unit	Note
SPI_MOSI output—Master data hold time	t_{NIKHOX}	0.5	—	ns	3
	t_{NIKHOX}	4.0			4
SPI_MOSI output—Master data delay	t_{NIKHOV}	—	6.0	ns	3
	t_{NIKHOV}		7.4		4
SPI_CS outputs—Master data hold time	$t_{NIKHOX2}$	0	—	ns	—

2.9.1 Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1000 Mbps) — FIFO/GMII/MII/TBI/RGMII/RTBI/RMII Electrical Characteristics

The electrical characteristics specified here apply to all FIFO mode, gigabit media independent interface (GMII), media independent interface (MII), ten-bit interface (TBI), reduced gigabit media independent interface (RGMII), reduced ten-bit interface (RTBI), and reduced media independent interface (RMII) signals except management data input/output (MDIO) and management data clock (MDC), and serial gigabit media independent interface (SGMII). The RGMII, RTBI and FIFO mode interfaces are defined for 2.5 V, while the GMII, MII, RMII, and TBI interfaces can operate at 3.3V.

The GMII, MII, or TBI interface timing is compliant with IEEE 802.3. The RGMII and RTBI interfaces follow the Reduced Gigabit Media-Independent Interface (RGMII) Specification Version 1.3 (12/10/2000). The RMII interface follows the RMII Consortium RMII Specification Version 1.2 (3/20/1998).

The electrical characteristics for MDIO and MDC are specified in Section 2.10, "Ethernet Management Interface Electrical Characteristics."

The electrical characteristics for SGMII is specified in Section 2.9.3, "SGMII Interface Electrical Characteristics." The SGMII interface conforms (with exceptions) to the Serial-GMII Specification Version 1.8.

2.9.1.1 GMII, MII, TBI, RGMII, RMII and RTBI DC Electrical Characteristics

All GMII, MII, TBI, RGMII, RMII and RTBI drivers and receivers comply with the DC parametric attributes specified in the following tables. The RGMII and RTBI signals are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 24. GMII, MII, RMII, and TBI DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
Supply voltage 3.3 V	LV_{DD} TV_{DD}	3.13	3.47	V	1, 2
Output high voltage (LV_{DD}/TV_{DD} = Min, IOH = –4.0 mA)	VOH	2.40	LV_{DD}/TV_{DD} + 0.3	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, IOL = 4.0 mA)	VOL	GND	0.50	V	—
Input high voltage	V_{IH}	1.90	LV_{DD}/TV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	0.90	V	—
Input high current (V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IH}	—	40	µA	1, 2,3
Input low current (V_{IN} = GND)	I_{IL}	–600	—	µA	3

Notes:

1 LV_{DD} supports eTSECs 1.

2 TV_{DD} supports eTSECs 3.

3 The symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

This figure shows the RGMII and RTBI AC timing and multiplexing diagrams.

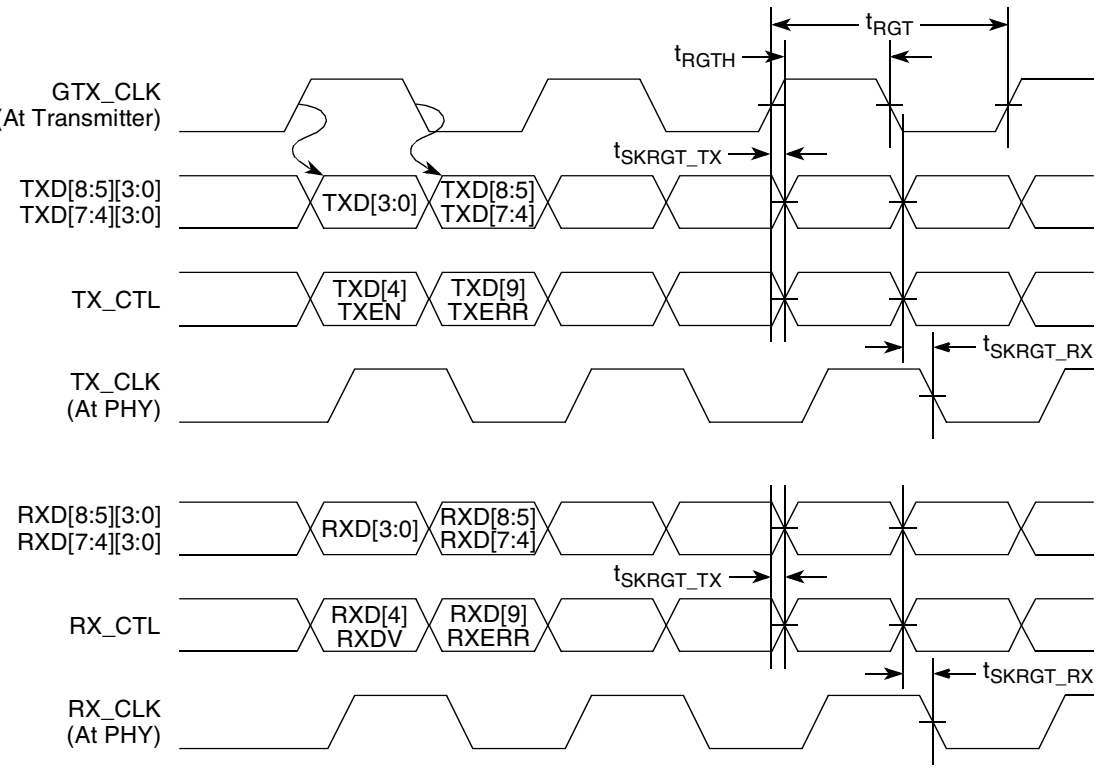


Figure 25. RGMII and RTBI AC Timing and Multiplexing Diagrams

2.9.2.7 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

2.9.2.7.1 RMII Transmit AC Timing Specifications

The RMII transmit AC timing specifications are in the following table.

Table 36. RMII Transmit AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
TSECn_TX_CLK clock period	t_{RMT}	15.0	20.0	25.0	ns
TSECn_TX_CLK duty cycle	t_{RMTH}	35	50	65	%
TSECn_TX_CLK peak-to-peak jitter	t_{RMTJ}	—	—	250	ps

When operating in SGMII mode, the eTSEC EC_GTX_CLK125 clock is not required for this port. Instead, SerDes reference clock is required on SD2_REF_CLK and $\overline{\text{SD2\_REF\_CLK}}$ pins.

2.9.3.1 DC Requirements for SGMII SD2_REF_CLK and SD2_REF_CLK

The characteristics and DC requirements of the separate SerDes reference clock are described in Section 2.20, "High-Speed Serial Interfaces."

2.9.3.2 AC Requirements for SGMII SD2_REF_CLK and $\overline{\text{SD2\_REF\_CLK}}$

This table lists the SGMII SerDes reference clock AC requirements. Please note that SD2_REF_CLK and $\overline{\text{SD2\_REF\_CLK}}$ are not intended to be used with, and should not be clocked by, a spread spectrum clock source.

Table 38. SD2_REF_CLK and $\overline{\text{SD2\_REF\_CLK}}$ AC Requirements

Symbol	Parameter Description	Min	Typical	Max	Units	Notes
t_{REF}	REFCLK cycle time	—	10 (8)	—	ns	1
t_{REFCJ}	REFCLK cycle-to-cycle jitter. Difference in the period of any two adjacent REFCLK cycles	—	—	100	ps	—
t_{REFPJ}	Phase jitter. Deviation in edge location with respect to mean edge location	–50	—	50	ps	2,3

Notes:

1. 8 ns applies only when 125 MHz SerDes2 reference clock frequency is selected via cfg_srds_sgmii_refclk during POR.
2. In a frequency band from 150 kHz to 15 MHz, at BER of 10E-12.
3. Total peak-to-peak deterministic jitter "Dj" should be less than or equal to 50 ps.

Table 40. SGMII DC Receiver Electrical Characteristics (continued)

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Receiver differential input impedance	Z_{RX_DIFF}	80	100	120	Ω	—
Receiver common mode input impedance	Z_{RX_CM}	20	—	35	Ω	—
Common mode input voltage	V_{CM}	—	$V_{xcorevss}$	—	V	6

Notes:
1. Input must be externally AC-coupled.
2. $V_{RX\_DIFFp\text{-}p}$ is also referred to as peak to peak input differential voltage
3. The concept of this parameter is equivalent to the Electrical Idle Detect Threshold parameter in PCI Express. See Table 72 for further explanation.
4. The LSTS shown in the table refers to the LSTSA or LSTSE bit field of chip's SerDes 2 control register.
5. $V_{CM\_ACp\text{-}p}$ is also referred to as peak to peak AC common mode voltage.
6. On-chip termination to S2GND (xcorevss).

2.9.3.4 SGMII AC Timing Specifications

This section describes the SGMII transmit and receive AC timing specifications. Transmitter and receiver characteristics are measured at the transmitter outputs (SD2_TX[n] and $\overline{\text{SD2\_TX}}$[n]) or at the receiver inputs (SD2_RX[n] and $\overline{\text{SD2\_RX}}$[n]) as depicted in Figure 32 respectively.

2.9.3.4.1 SGMII Transmit AC Timing Specifications

This table provides the SGMII transmit AC timing targets. A source synchronous clock is not provided.

Table 41. SGMII Transmit AC Timing Specifications

At recommended operating conditions with $X2V_{DD}$ = 1.0V ± 5%.

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Deterministic Jitter	JD	—	—	0.17	UI p-p	—
Total Jitter	JT	—	—	0.35	UI p-p	—
Unit Interval	UI	799.92	800	800.08	ps	1
V_{OD} fall time (80%-20%)	tfall	50	—	120	ps	—
V_{OD} rise time (20%-80%)	t_{rise}	50	—	120	ps	—

Notes:
1. Each UI is 800 ps ± 100 ppm.

Table 52. Local Bus General Timing Parameters (BV_{DD} = 2.5 V DC) (continued)

Parameter	Configuration	Symbol [1]	Min	Max	Unit	Notes
Output hold from local bus clock for LAD/LDP	—	$t_{LBKHOX2}$	0.8	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	—	$t_{LBKHOZ1}$	—	2.6	ns	5
Local bus clock to output high impedance for LAD/LDP	—	$t_{LBKHOZ2}$	—	2.6	ns	5

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 2.5-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is guaranteed with LBCR[AHD] = 0.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.

This table describes the general timing parameters of the local bus interface at BV_{DD} = 1.8 V DC.

Table 53. Local Bus General Timing Parameters (BV_{DD} = 1.8 V DC)

Parameter	Configuration	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time	—	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	—	t_{LBKH}/t_{LBK}	43	57	%	
LCLK[n] skew to LCLK[m] or LSYNC_OUT	—	$t_{LBKSKEW}$		150	ps	7
Input setup to local bus clock (except LUPWAIT)	—	$t_{LBIVKH1}$	2.4	—	ns	3, 4
LUPWAIT input setup to local bus clock	—	$t_{LBIVKH2}$	1.9	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	—	$t_{LBIXKH1}$	1.1	—	ns	3, 4
LUPWAIT input hold from local bus clock	—	$t_{LBIXKH2}$	1.1	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH setup and hold time)	—	t_{LBOTOT}	1.2	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	—	$t_{LBKHOV1}$	—	3.2	ns	—
Local bus clock to data valid for LAD/LDP	—	$t_{LBKHOV2}$	—	3.2	ns	3
Local bus clock to address valid for LAD	—	$t_{LBKHOV3}$	—	3.2	ns	3
Local bus clock to LALE assertion	—	$t_{LBKHOV4}$	—	3.2	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	—	$t_{LBKHOX1}$	0.9	—	ns	3

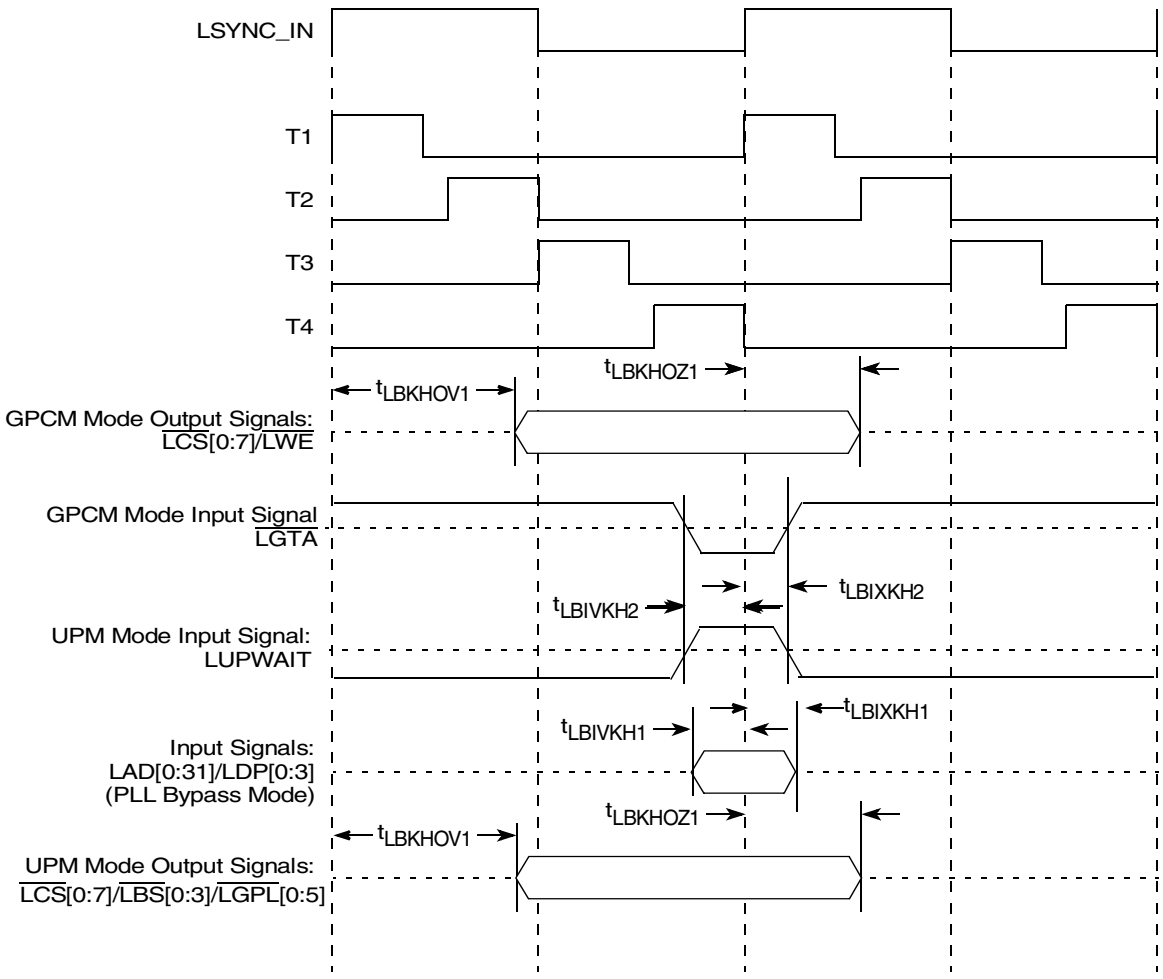


Figure 42. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 8 or 16(PLL Enabled)

2.13 Enhanced Secure Digital Host Controller (eSDHC)

This section describes the DC and AC electrical specifications for the eSDHC interface of the chip.

2.13.1 eSDHC DC Electrical Characteristics

This table provides the DC electrical characteristics for the eSDHC interface of the chip.

Table 55. eSDHC interface DC Electrical Characteristics

At recommended operating conditions (see Table 3)

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Input high voltage	V_{IH}	—	0.625 * OVDD	OVDD+0.3	V	—
Input low voltage	V_{IL}	—	–0.3	0.25 * OVDD	V	—
Input/Output leakage current	I_{IN}/I_{OZ}	—	–10	10	uA	—
Output high voltage	V_{OH}	I_{OH} = -100 uA @OVDDmin	0.75 * OVDD	—	V	—

2.16.1 Requirements for SATA REF_CLK

The AC requirements for the SATA reference clock are listed in the following table.

Table 59. Reference Clock Input Requirements

Parameter	Symbol	Min	Typical	Max	Unit	Notes
SD2_REF_CLK/_B reference clock cycle time	t_{CLK_REF}	100	—	150	MHz	1
SD2_REF_CLK/_B frequency tolerance	t_{CLK_TOL}	–350	0	+350	ppm	—
SD_REF_CLK/_B rise/fall time (80%-20%)	$t_{CLK\_RISE}/t_{CLK\_FALL}$	—	—	1	ns	—
SD_REF_CLK/_B duty cycle (@50% X2VDD)	t_{CLK_DUTY}	45	50	55	%	—
SD_REF_CLK/_B cycle to cycle clock jitter (period jitter)	t_{CLK_CJ}	—	—	100	ps	—
SD_REF_CLK/_B phase jitter (peak-to-peak)	t_{CLK_PJ}	–50	—	+50	ps	2,3

Note:

1. Only 100/125/150 MHz have been tested, other in between values will not work correctly with the rest of the system.
2. In a frequency band from 150 kHz to 15 MHz, at BER of 10E-12.
3. Total peak-to-peak deterministic jitter “Dj” should be less than or equal to 50 ps.

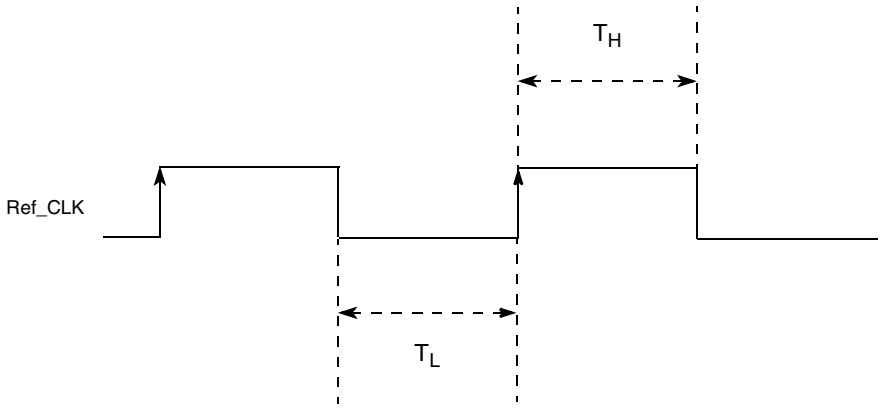


Figure 49. Reference Clock Timing Waveform

2.18 GPIO

This section describes the DC and AC electrical specifications for the GPIO interface of the chip.

2.18.1 GPIO DC Electrical Characteristics

This table provides the DC electrical characteristics for the GPIO interface.

Table 65. GPIO DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	– 0.3	0.8	V
Input current (V_{IN} [1] = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:

1. The symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

2.18.2 GPIO AC Electrical Specifications

This table provides the GPIO input and output AC timing specifications.

Table 66. GPIO Input and Output AC Timing Specifications[1]

Characteristic	Symbol [2]	Min	Unit	Notes
GPIO inputs—minimum pulse width	t_{PIWID}	7.5	ns	3
GPIO outputs—minimum pulse width	t_{GTOWID}	12	ns	—

Notes:

1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by any external synchronous logic. GPIO inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation.
3. The minimum pulse width is a function of the MPX/Platform clock. The minimum pulse width must be greater than or equal to 4 times the MPX/Platform clock period.

This figure provides the AC test load for the GPIO.

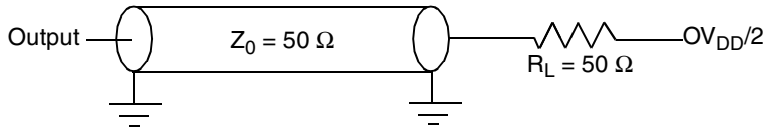


Figure 53. GPIO AC Test Load

2.23.1 Clock Ranges

This table provides the clocking specifications for the processor cores and Table 74 provides the clocking specifications for the memory bus.

Table 73. Processor Core Clocking Specifications

Characteristic	Maximum Processor Core Frequency								Unit	Notes
	600 MHz		800 MHz		1000 MHz		1250 MHz			
	Min	Max	Min	Max	Min	Max	Min	Max		
e500 core processor frequency	600	600	600	800	600	1000	600	1250	MHz	1, 2
CCB frequency	400	400	400	400	333	400	333	500		
DDR Data Rate	400	400	400	400	400	400	400	500		

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. See Section 2.23.2, “CCB/SYSCLK PLL Ratio,” Section 2.23.3, “e500 Core PLL Ratio,“and Section 2.23.4, “DDR/DDRCLK PLL Ratio,” for ratio settings.
2. The processor core frequency speed bins listed also reflect the maximum platform (CCB) and DDR data rate frequency supported by production test. Running CCB and/or DDR data rate higher than the limit shown above, although logically possible via valid clock ratio setting in some condition, is not supported.

The DDR memory controller can run in either synchronous or asynchronous mode. When running in synchronous mode, the memory bus is clocked relative to the platform clock frequency. When running in asynchronous mode, the memory bus is clocked with its own dedicated PLL. This table provides the clocking specifications for the memory bus.

Table 74. Memory Bus Clocking Specifications

Characteristic	Maximum Processor Core Frequency		Unit	Notes
	600, 800, 1000, 1250			
	Min	Max		
DDR Memory bus clock speed	200	250	MHz	1, 2, 3, 4

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 2.23.2, “CCB/SYSCLK PLL Ratio,” Section 2.23.3, “e500 Core PLL Ratio,” and Section 2.23.4, “DDR/DDRCLK PLL Ratio,” for ratio settings.
2. The Memory bus clock refers to the chip’s memory controllers’ MCK[0:5] and $\overline{\text{MCK}}$[0:5] output clocks, running at half of the DDR data rate.
3. In synchronous mode, the memory bus clock speed is half the platform clock frequency. In other words, the DDR data rate is the same as the platform (CCB) frequency. If the desired DDR data rate is higher than the platform (CCB) frequency, asynchronous mode must be used.
4. In asynchronous mode, the memory bus clock speed is dictated by its own PLL. See Section 2.23.4, “DDR/DDRCLK PLL Ratio.” The memory bus clock speed must be less than or equal to the CCB clock rate which in turn must be less than the DDR data rate.

2.23.2 CCB/SYSCLK PLL Ratio

The CCB clock is the clock that drives the e500 core complex bus (CCB), and is also called the platform clock. The frequency of the CCB is set using the following reset signals, as shown in the following table:

- SYSCLK input signal
- Binary value on LA[28:31] at power up

Note that there is no default for this PLL ratio; these signals must be pulled to the desired values.

Table 75. CCB Clock Ratio

Binary Value of LA[28:31] Signals	CCB:SYSCLK Ratio	Binary Value of LA[28:31] Signals	CCB:SYSCLK Ratio
0000	Reserved	1000	8:1
0001	Reserved	1001	9:1
0010	Reserved	1010	10:1
0011	3:1	1011	Reserved
0100	4:1	1100	12:1
0101	5:1	1101	Reserved
0110	6:1	1110	Reserved
0111	Reserved	1111	Reserved

2.23.3 e500 Core PLL Ratio

This table describes the clock ratio between the e500 core complex bus (CCB) and the e500 core clock. This ratio is determined by the binary value of LBCTL, LALE and LGPL2 at power up, as shown in this table.

Table 76. e500 Core to CCB Clock Ratio

Binary Value of LBCTL, LALE, LGPL2 Signals	e500 core: CCB Clock Ratio	Binary Value of LBCTL, LALE, LGPL2 Signals	e500 core: CCB Clock Ratio
000	4:1	100	2:1
001	9:2	101	5:2
010	Reserved	110	3:1
011	3:2	111	7:2

2.23.4 DDR/DDRCLK PLL Ratio

The DDR memory controller complex can be synchronous with, or asynchronous to, the CCB, depending on configuration.

The following table describes the clock ratio between the DDR memory controller complex and the DDR/DDRCLK PLL reference clock, DDRCLK, which is not the memory bus clock.

When synchronous mode is selected, the memory buses are clocked at half the CCB clock rate. The default mode of operation is for the DDR data rate for the DDR controller to be equal to the CCB clock rate in synchronous mode, or the resulting DDR PLL rate in asynchronous mode.

In asynchronous mode, the DDR PLL rate to DDRCLK ratios listed in Table 77 reflects the DDR data rate to DDRCLK ratio, since the DDR PLL rate in asynchronous mode means the DDR data rate resulting from DDR PLL output.

The heat sink removes most of the heat from the chip for most applications. Heat generated on the active side of the chip is conducted through the silicon and through the heat sink attach material (or thermal interface material), and finally to the heat sink. The junction-to-case thermal resistance is low enough that the heat sink attach material and heat sink thermal resistance are the dominant terms.

2.24.3.2 Thermal Interface Materials

A thermal interface material is required at the package-to-heat sink interface to minimize the thermal contact resistance. The performance of thermal interface materials improves with increased contact pressure. This performance characteristic chart is generally provided by the thermal interface vendors.

3 Hardware Design Considerations

This section provides electrical and thermal design recommendations for successful application of the chip.

3.1 System Clocking

This chip includes seven PLLs:

- The platform PLL generates the platform clock from the externally supplied SYSCLK input. The frequency ratio between the platform and SYSCLK is selected using the platform PLL ratio configuration bits as described in Section 2.23.2, “CCB/SYSCLK PLL Ratio.”
- The e500 core PLL generates the core clock as a slave to the platform clock. The frequency ratio between the e500 core clock and the platform clock is selected using the e500 PLL ratio configuration bits as described in Section 2.23.3, “e500 Core PLL Ratio.”
- The PCI PLL generates the clocking for the PCI bus
- The local bus PLL generates the clock for the local bus.
- There is a PLL for the SerDes1 block to be used for PCI Express interface
- There is a PLL for the SerDes2 block to be used for SGMII and SATA interfaces.
- The DDR PLL generates the DDR clock from the externally supplied DDRCLK input in asynchronous mode. The frequency ratio between the DDR clock and DDRCLK is described in Section 2.23.4, “DDR/DDRCLK PLL Ratio.”

3.2 Power Supply Design and Sequencing

3.2.1 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins (AV_{DD}_PLAT, AV_{DD}_CORE, AV_{DD}_PCI, AV_{DD}_LBIU, and AV_{DD}_SRDS respectively). The AV_{DD} level should always be equivalent to V_{DD}, and preferably these voltages will be derived directly from V_{DD} through a low frequency filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide independent filter circuits per PLL power supply as illustrated in Figure 75, one to each of the AV_{DD} pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum Effective Series Inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

Each circuit should be placed as close as possible to the specific AV_{DD} pin being supplied to minimize noise coupled from nearby circuits. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of 783 FC-PBGA the footprint, without the inductance of vias.